

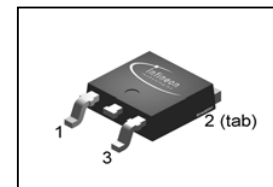
OptiMOS® -T2 Power-Transistor

Product Summary

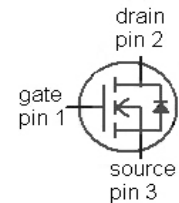
V_{DS}	30	V
$R_{DS(on),max}$	4.3	mΩ
I_D	70	A

Features

- N-channel - Enhancement mode
- Automotive AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green product (RoHS compliant)
- Ultra low Rds(on)
- 100% Avalanche tested

PG-TO252-3-11


Type	Package	Marking
IPD70N03S4L-04	PG-TO252-3-11	4N03L04


Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current ¹⁾	I_D	$T_C=25\text{ °C}, V_{GS}=10\text{ V}$	70	A
		$T_C=100\text{ °C}, V_{GS}=10\text{ V}^{2)}$	70	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_C=25\text{ °C}$	280	
Avalanche energy, single pulse	E_{AS}	$I_D=70\text{ A}$	57	mJ
Avalanche current, single pulse	I_{AS}	$T_C=25\text{ °C}$	70	A
Gate source voltage	V_{GS}		±16	V
Power dissipation	P_{tot}	$T_C=25\text{ °C}$	68	W
Operating and storage temperature	T_j, T_{stg}		-55 ... +175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics²⁾						
Thermal resistance, junction - case	R_{thJC}		-	-	2.2	K/W
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	62	
		6 cm ² cooling area ³⁾	-	-	40	

Electrical characteristics, at $T_j=25\text{ }^\circ\text{C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$	30	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=30\text{ }\mu\text{A}$	1.0	1.5	2.2	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=30\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ }^\circ\text{C}$	-	0.01	1	μA
		$V_{DS}=30\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ }^\circ\text{C}^{2)}$	-	10	1000	
		$V_{DS}=18\text{ V}, V_{GS}=0\text{ V}, T_j=85\text{ }^\circ\text{C}^{2)}$	-	5	60	
Gate-source leakage current	I_{GSS}	$V_{GS}=16\text{ V}, V_{DS}=0\text{ V}$	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=4.5\text{ V}, I_D=35\text{ A}$	-	4.9	5.7	m Ω
		$V_{GS}=10\text{ V}, I_D=70\text{ A}$	-	3.6	4.3	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics²⁾

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$ $f=1\text{ MHz}$	-	2500	3300	pF
Output capacitance	C_{oss}		-	640	830	
Reverse transfer capacitance	C_{rss}		-	35	70	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=15\text{ V}, V_{GS}=10\text{ V},$ $I_D=70\text{ A}, R_G=3.5\ \Omega$	-	7	-	ns
Rise time	t_r		-	5	-	
Turn-off delay time	$t_{d(off)}$		-	27	-	
Fall time	t_f		-	5	-	

Gate Charge Characteristics²⁾

Gate to source charge	Q_{gs}	$V_{DD}=24\text{ V}, I_D=70\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	8	10	nC
Gate to drain charge	Q_{gd}		-	5	10	
Gate charge total	Q_g		-	37	48	
Gate plateau voltage	$V_{plateau}$		-	3.2	-	V

Reverse Diode

Diode continuous forward current ²⁾	I_S	$T_C=25\text{ }^\circ\text{C}$	-	-	80	A
Diode pulse current ²⁾	$I_{S,pulse}$		-	-	280	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=70\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	0.6	0.95	1.3	V
Reverse recovery time ²⁾	t_{rr}	$V_R=15\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	40	-	ns
Reverse recovery charge ²⁾	Q_{rr}		-	35	-	

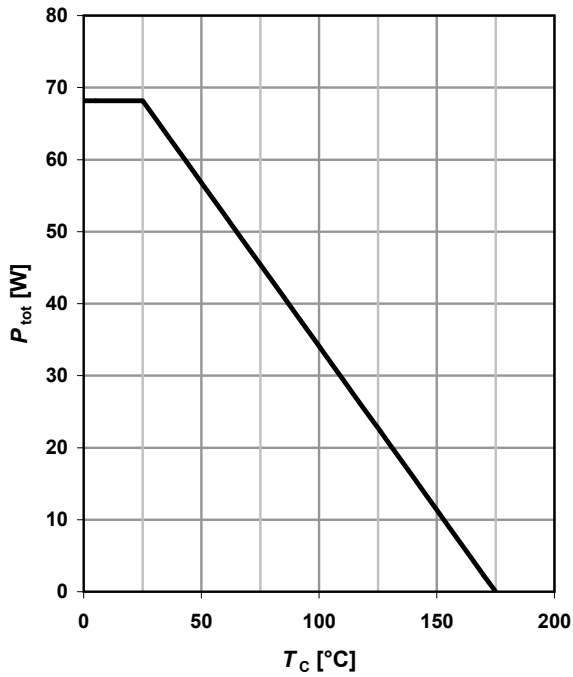
¹⁾ Current is limited by bondwire; with an $R_{thJC} = 2.2\text{K/W}$ the chip is able to carry 100A at 25°C. For detailed information see Application Note ANPS071E at www.infineon.com/optimos

²⁾ Defined by design. Not subject to production test.

³⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

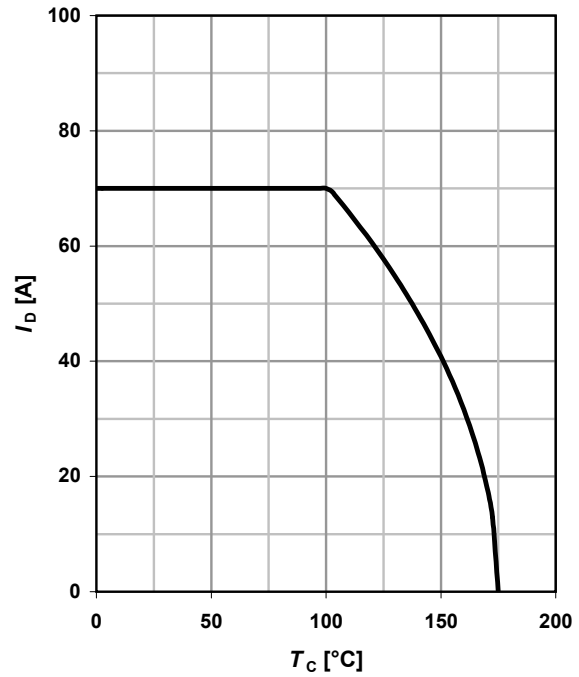
1 Power dissipation

$P_{tot} = f(T_c); V_{GS} \geq 6\text{ V}$



2 Drain current

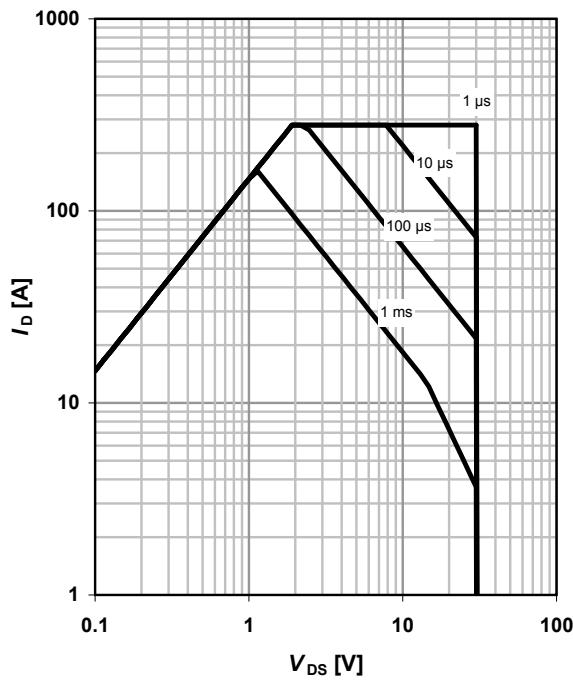
$I_D = f(T_c); V_{GS} \geq 6\text{ V}$



3 Safe operating area

$I_D = f(V_{DS}); T_c = 25\text{ °C}; D = 0$

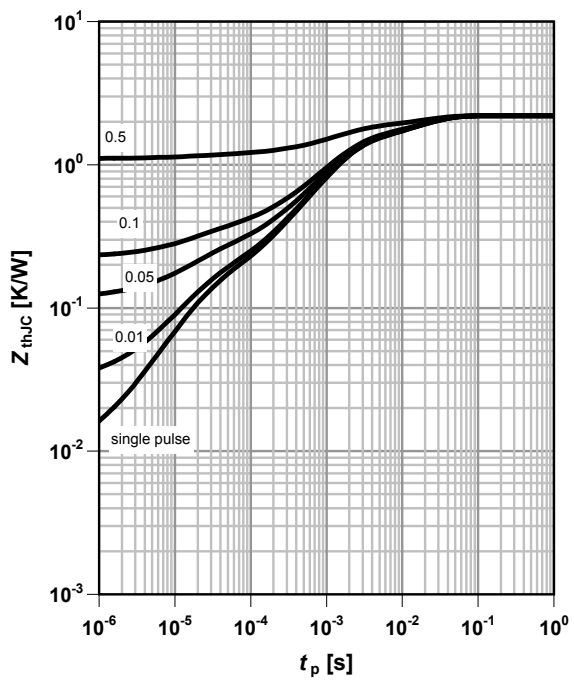
parameter: t_p



4 Max. transient thermal impedance

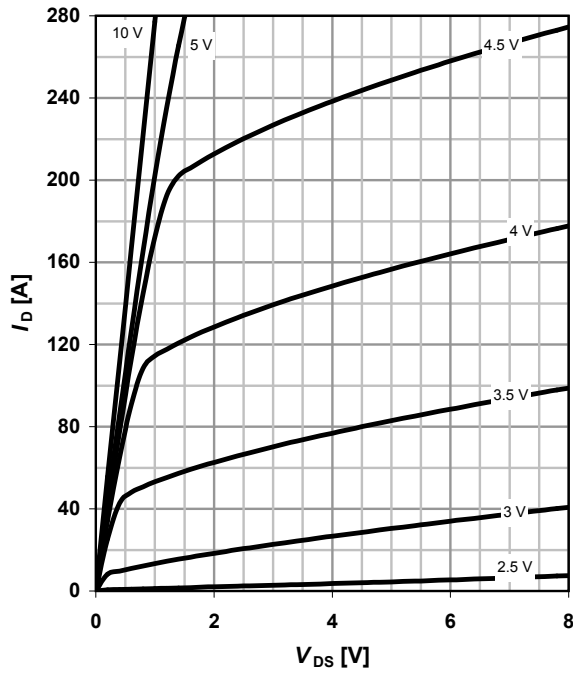
$Z_{thJC} = f(t_p)$

parameter: $D = t_p/T$

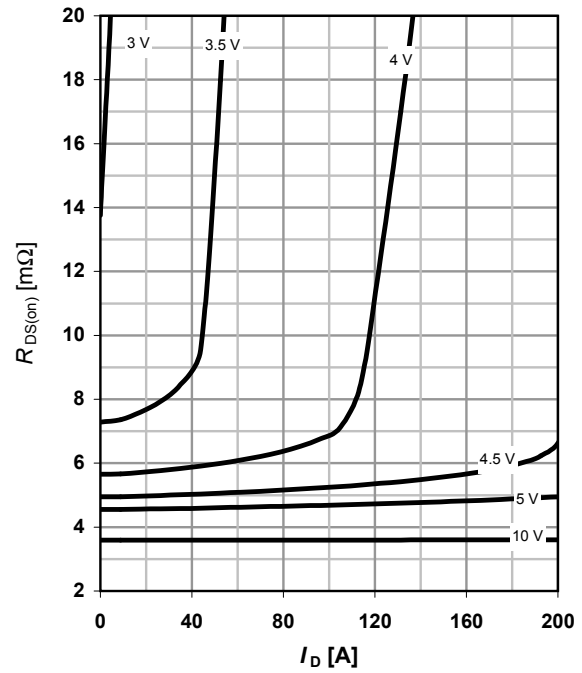


5 Typ. output characteristics

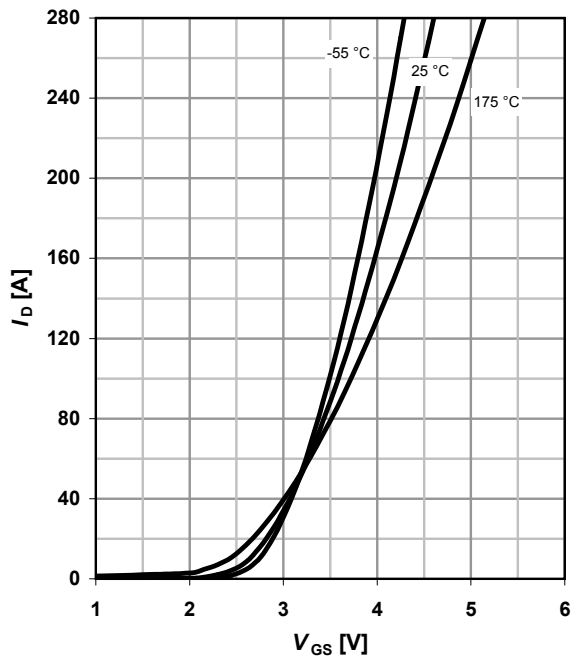
$$I_D = f(V_{DS}); T_j = 25\text{ °C}$$

 parameter: V_{GS}

6 Typ. drain-source on-state resistance

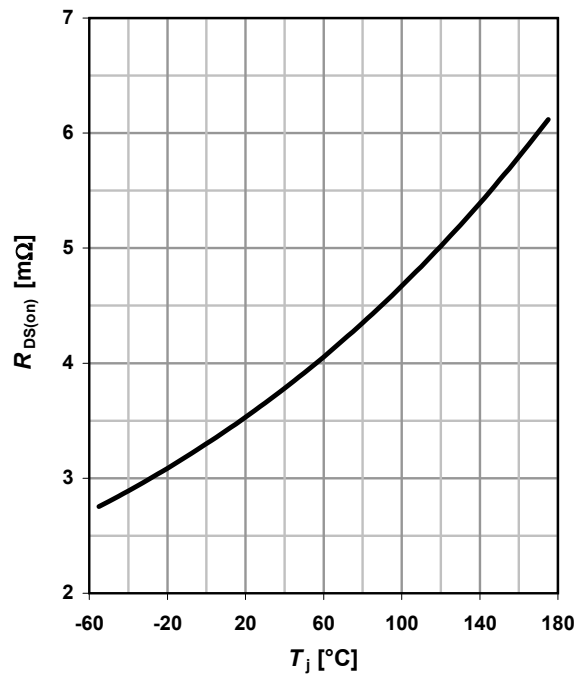
$$R_{DS(on)} = f(I_D); T_j = 25\text{ °C}$$

 parameter: V_{GS}

7 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} = 6V$$

 parameter: T_j

8 Typ. drain-source on-state resistance

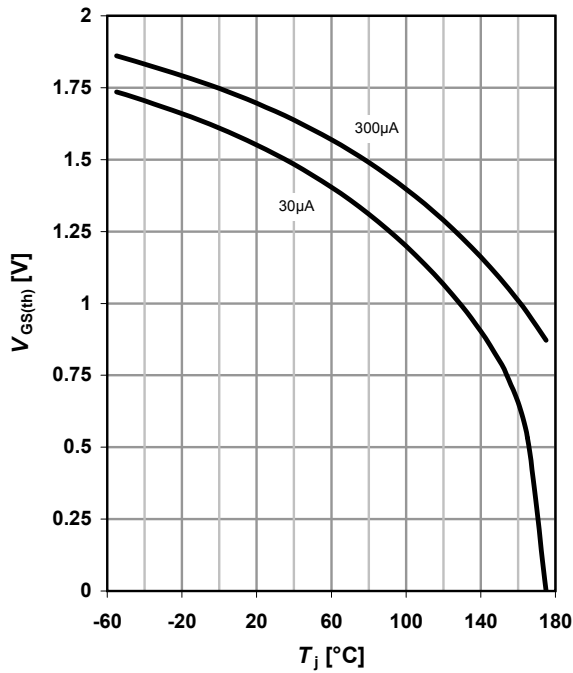
$$R_{DS(on)} = f(T_j); I_D = 70\text{ A}; V_{GS} = 10\text{ V}$$



9 Typ. gate threshold voltage

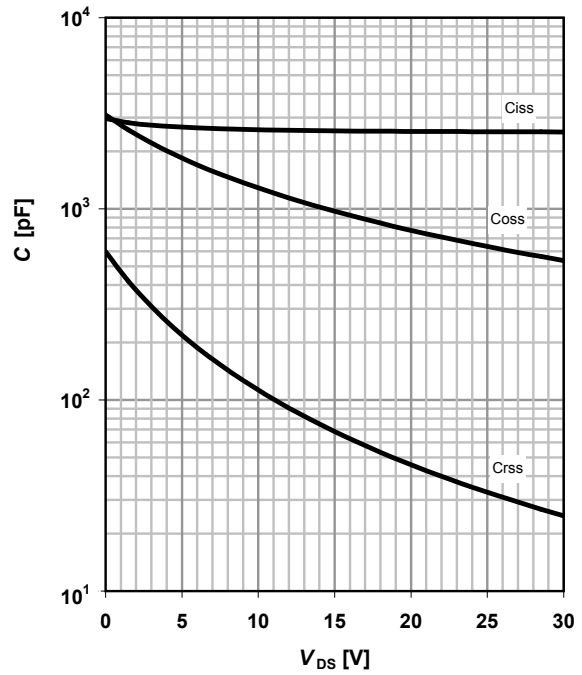
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

parameter: I_D



10 Typ. capacitances

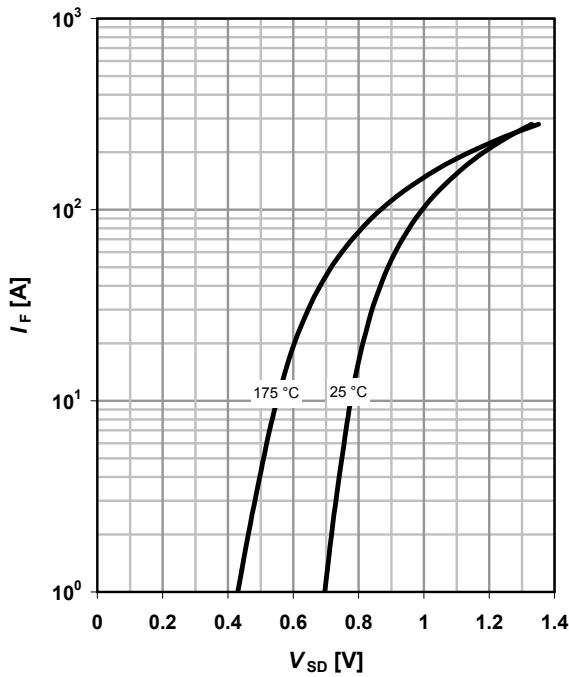
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



11 Typical forward diode characteristics

$$I_F = f(V_{SD})$$

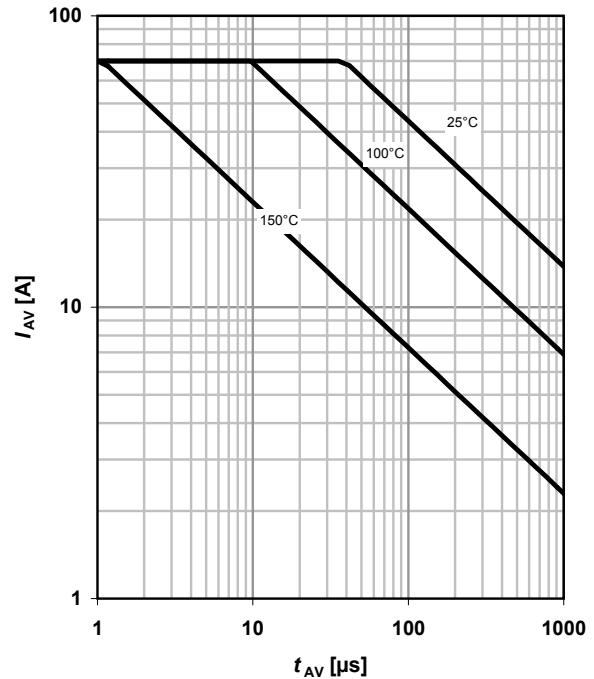
parameter: T_j



12 Typ. avalanche characteristics

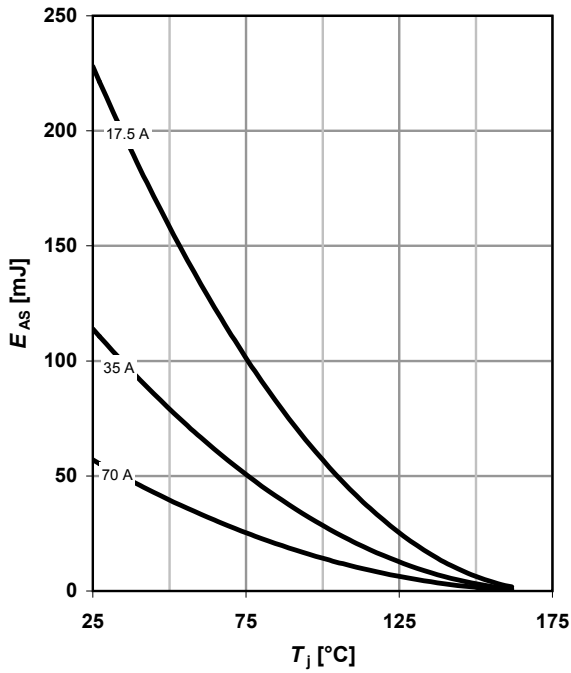
$$I_{AS} = f(t_{AV})$$

parameter: $T_{j(start)}$

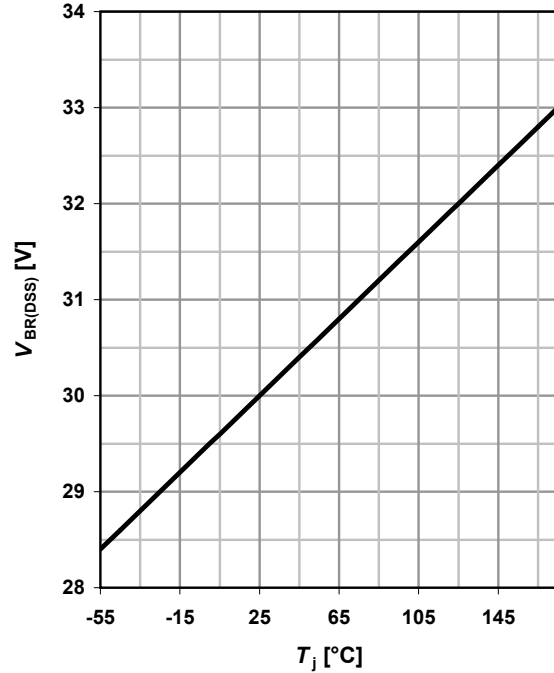


13 Typical avalanche energy

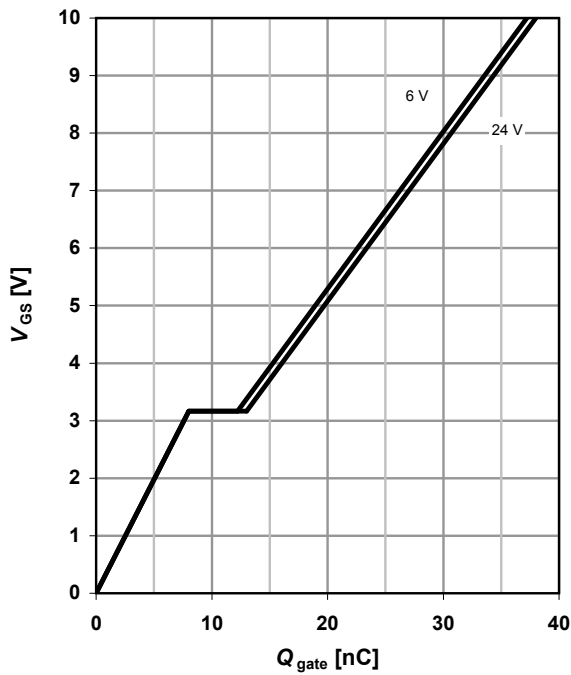
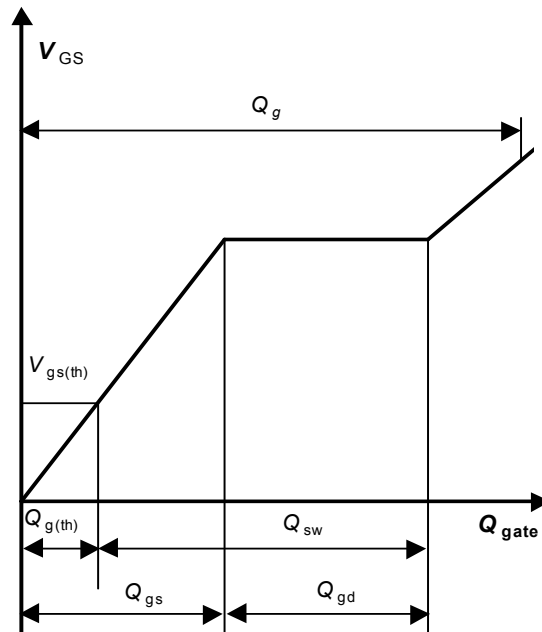
$$E_{AS} = f(T_j)$$

 parameter: I_D

14 Typ. drain-source breakdown voltage

$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$


15 Typ. gate charge

$$V_{GS} = f(Q_{gate}); I_D = 70 \text{ A pulsed}$$

 parameter: V_{DD}

16 Gate charge waveforms


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